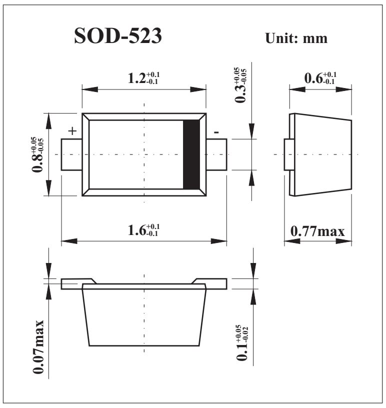
# Schottky barrier diode

# 1PS79SB31



## ■ Features

- ●Very Low forward voltage
- ● Guard ring protected
- ● Ultra small plastic SMD package.

## ■ Absolute Maximum Ratings Ta = 25℃

| Parameter | Symbol | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| continuous reverse voltage | $V_R$ | | | 30 | V |
| continuous forward current | $I_F$ | | | 200 | mA |
| repetitive peak forward current | $I_{FSM}$ | tp ≤ 1s;δ ≤ 0.5 | | 300 | mA |
| non-repetitive peak forwrad current | $I_{FSM}$ | t = 8.3 ms half sinewave;<br>JEDEC method | | 1000 | mA |
| storage temperature | $T_{stg}$ | | -65 | +150 | ℃ |
| junction temperature | $T_j$ | | | 125 | ℃ |
| operating ambient temperature | $T_{amb}$ | | -65 | +125 | ℃ |

## ■ Electrical Characteristics Ta = 25℃

| Parameter | Symbol | Conditions | Typ | Max | Unit |
|---|---|---|---|---|---|
| forward voltage | $V_F$ | $I_F$ = 0.1 mA | 130 | 190 | mV |
| | | $I_F$ = 1 mA | 190 | 250 | |
| | | $I_F$ = 10 mA | 255 | 300 | |
| | | $I_F$ = 100 mA | 355 | 410 | |
| | | $I_F$ = 200 mA | 420 | 500 | |
| capacitance reverse current | $I_R$ | $V_R$ = 10 V, note 1; | 2.5 | 30 | μ A |
| diods capacitance | $C_d$ | $V_R$ = 1 V, f = 1 MHz; | 20 | 25 | pF |

Note

1. Pulse test: pulse $t_p$ = 300 μ s, δ= 0.02.

## ■ Marking

| Marking | G3 |
|---|---|